

Each cell is a high-power LED chip with a current of 700 A.

High power

UV.

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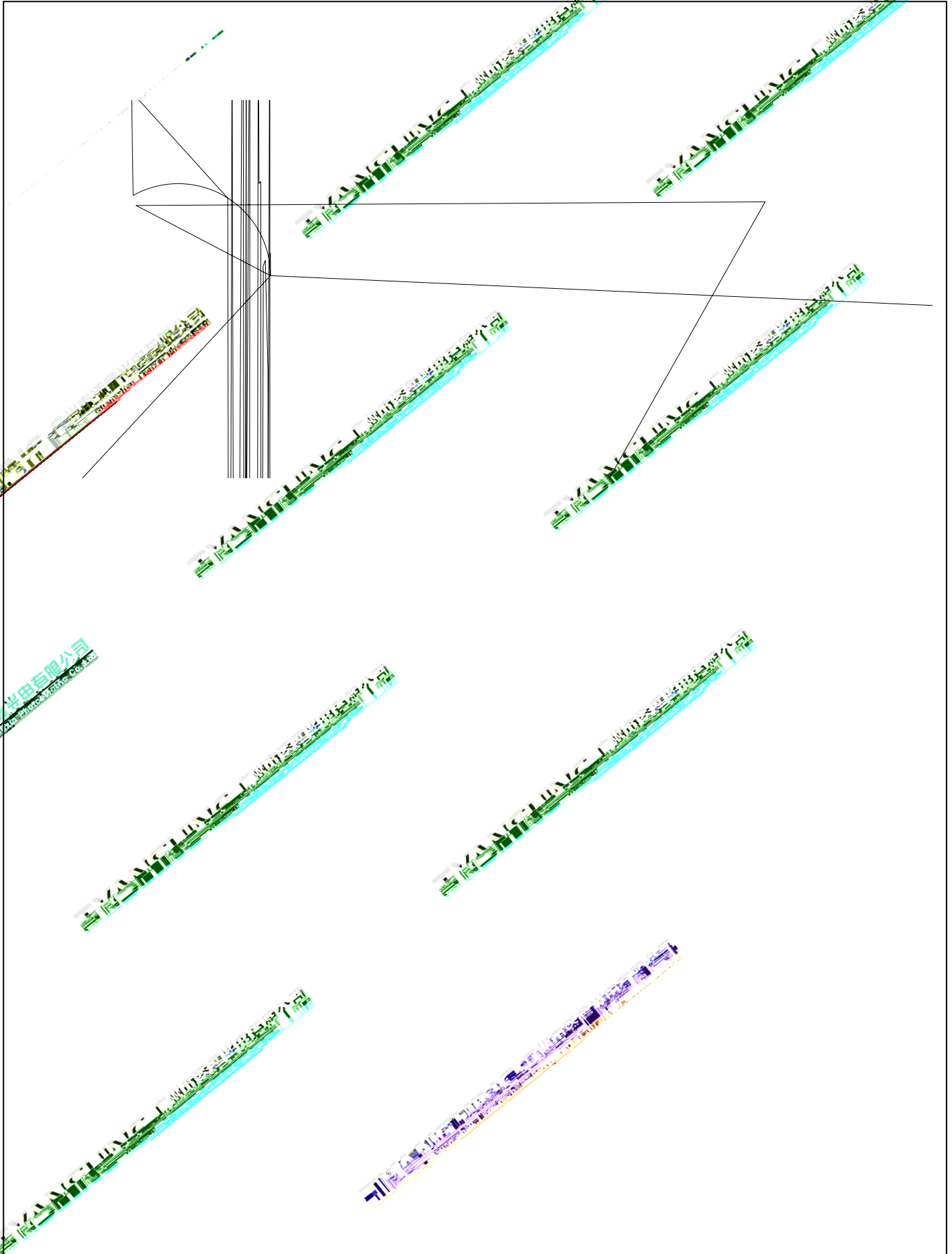
GaN

Ca

Powerful High

Ga diode light

Germanium light



Forward Current	IF	700	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	2640	W
Junction Temperature	Tj	150	
Electrostatic Discharge Threshold (ESD)	ESD	2000	V
Storage Temperature	Tg	-40 +70	
Operating Temperature	T	-30 +85	

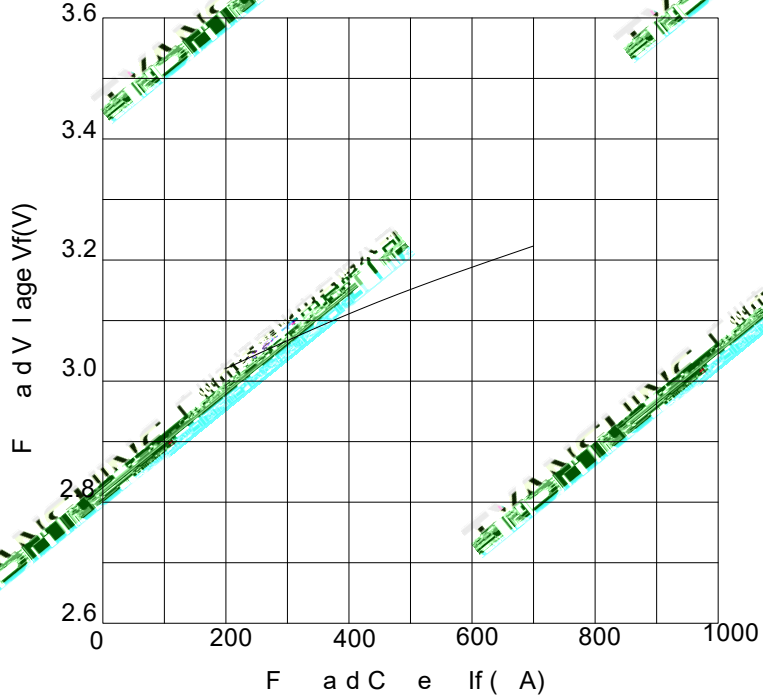
1. Specific application charge in use.
2. The data here specific reference to the actual data in accordance with the actual lead.
3. Precautions for ESD:
 STATIC SHIELD Electrostatic discharge the LED. Please do not use a anti-static bag for the LED. All devices, especially the delicate components should be stored in a static shield bag.

L i F l		If=350 A	55	70		l
Peak E i i Wa ele gh			497	502	507	
D i a Wa ele gh			500	505	510	
S ec al Li e Half-Wid h			17	22.5	27	
F a d V lage	V _f		2.8	3.1	3.3	V
Vie i g A gle a 50 IV	2 1/2		120		Deg	
Re e e C e	I _R			2	A	
The al Re i a ce J ci C a e	R _{J-C}				K/W	
Te e a e C efficie f V lage	V _{F/T}	If=350 A		-2	V/	

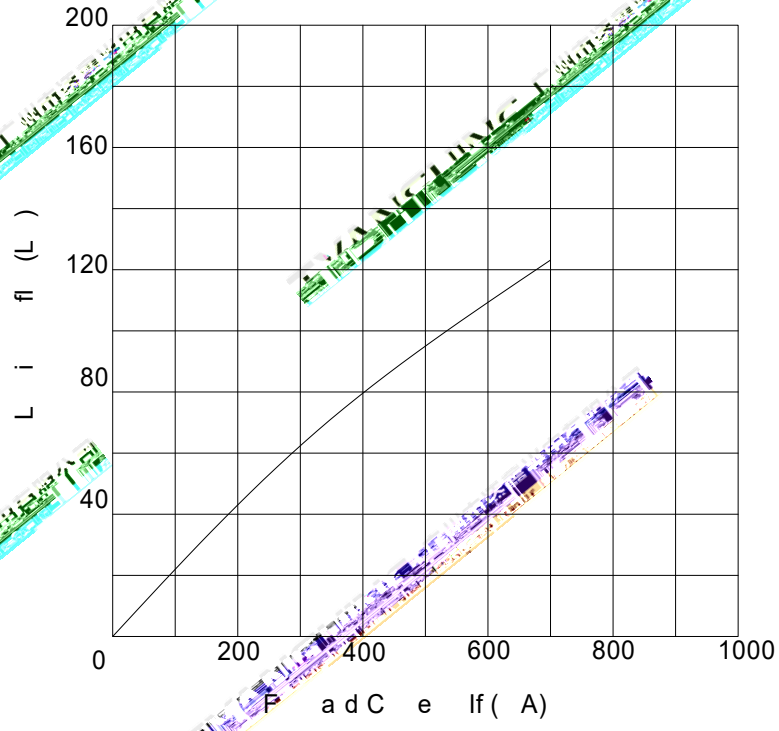
1. L i i e i i e a e d i h a ligh e a d file c b i a i h a a i a e h e C I E e e e e c e .
2. 1/2 i h e ff-a i a g l e a h i c h h e l i i e i i h a l f h e a i a l l i e i .
3. L i f l e a e e l e a c e : 15% .
4. F a d l a g e e a e e l e a c e : 0.15V .

(25 A bie Te ea eU le Ohe i eN ed)

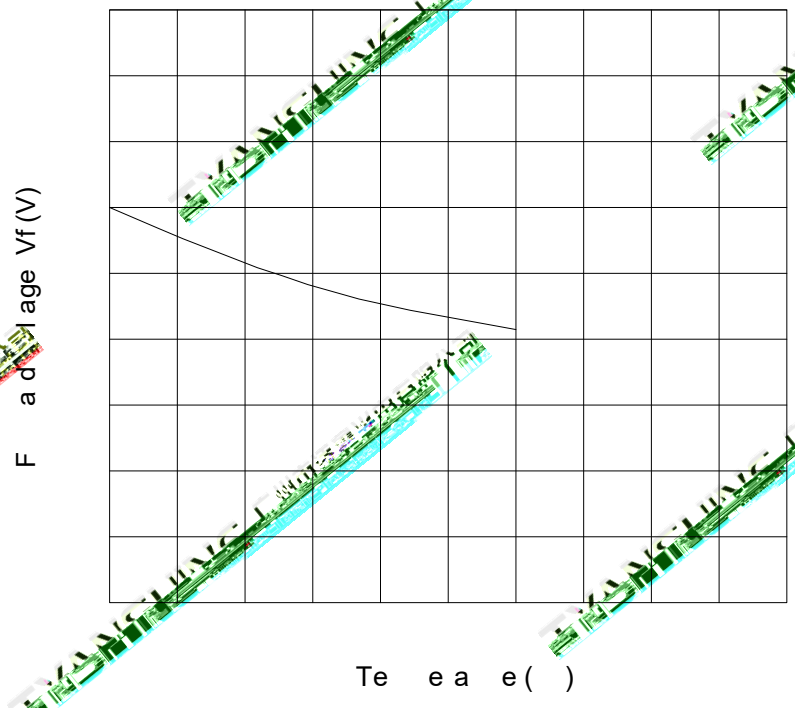
F a d C e VS. F a d V l a g e



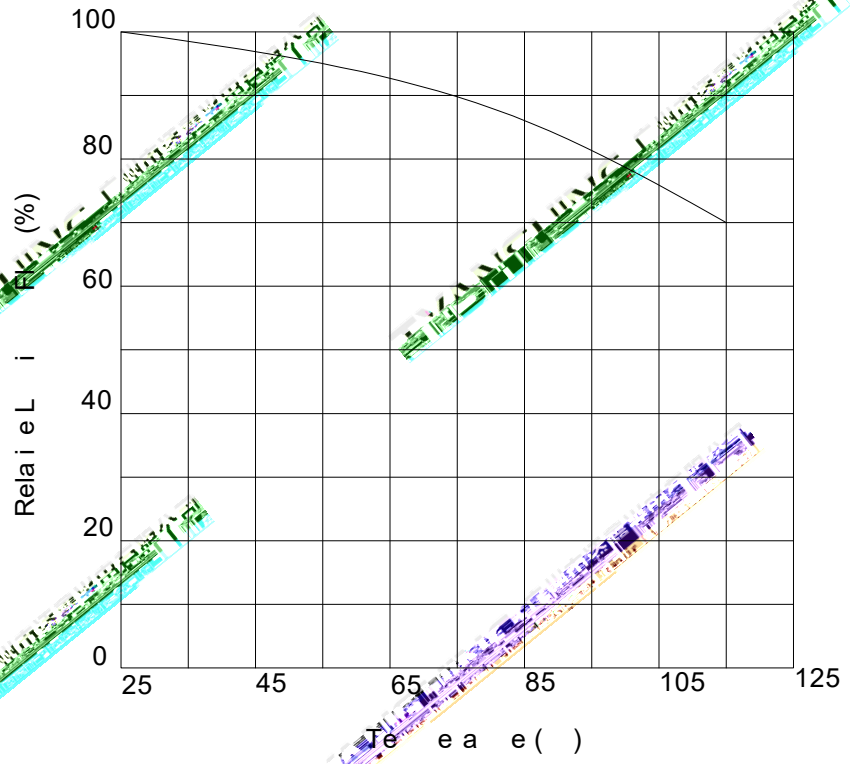
F a d C e VS. L i f l

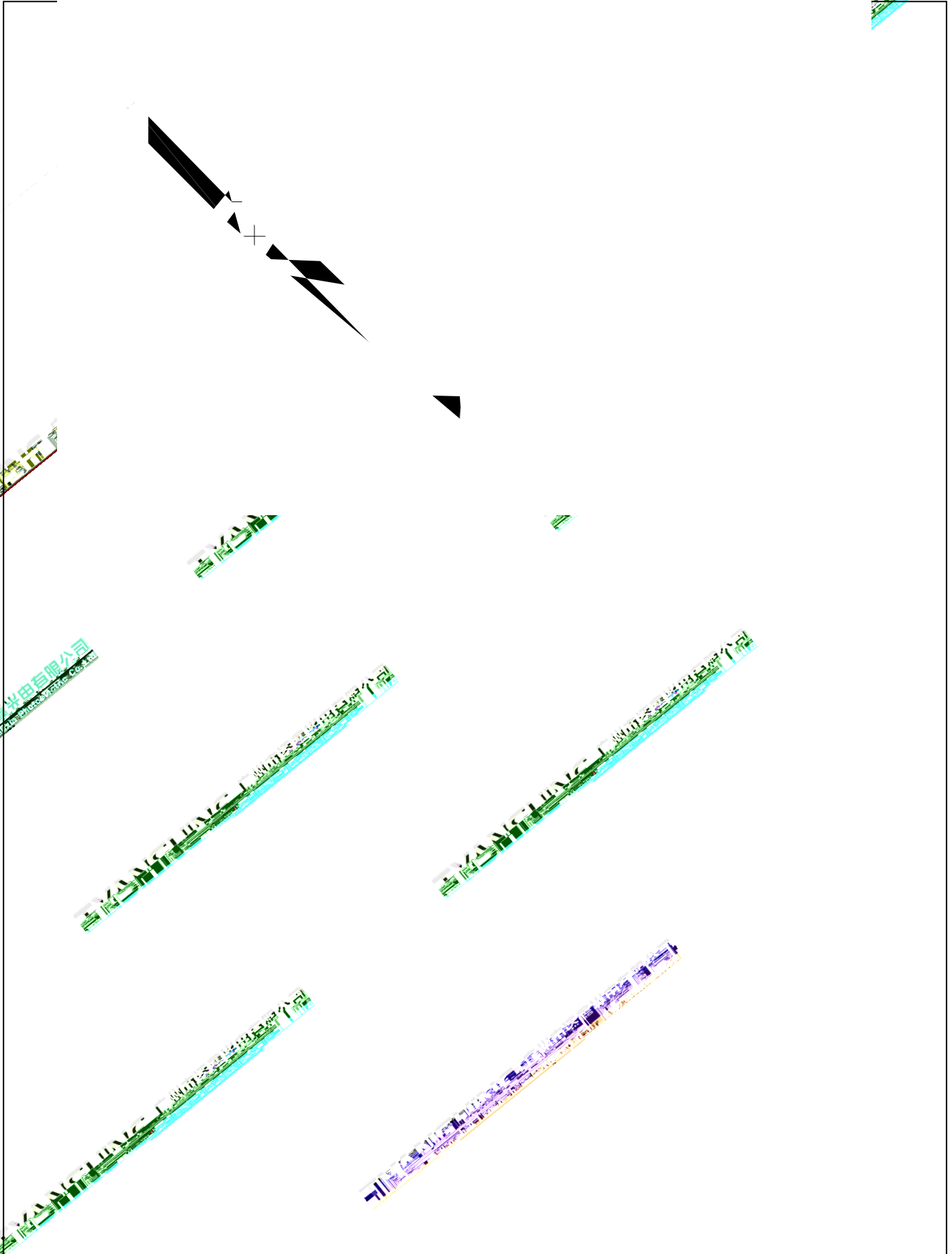


Te e a e VS. F a d V l a g e (IF=350 A)



Te e a e VS. R e l a i e L i F l (IF=350 A)





Temperature: 5 30 (41 86)

Humidity: 60% RH Max.

Use the circuit in the following figure.

